



# DATA SHEET

SEMICONDUCTOR

BCW70

## General Purpose Transistors

### PNP Silicon



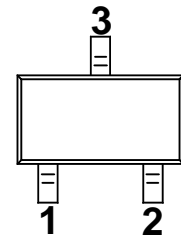
#### Features

Pb-Free Package is Available.

SOT-23 (TO-236AB)

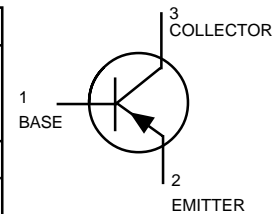
#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	-45	Vdc
Emitter-Base Voltage	$V_{EBO}$	-5.0	Vdc
Collector Current — Continuous	$I_C$	-100	mAdc



#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A = 25^\circ\text{C}$	$P_D$	225	mW
Derate above $25^\circ\text{C}$		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	$P_D$	300	mW
Derate above $25^\circ\text{C}$		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$



#### DEVICE MARKING

BCW69 = H1; BCW70 = H2

#### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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#### OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ( $I_C = -2.0 \text{ mAdc}, I_B = 0$ )	$V_{(BR)CEO}$	-45	—	Vdc
Collector-Emitter Breakdown Voltage ( $I_C = -100 \mu\text{Adc}, V_{EB} = 0$ )	$V_{(BR)CES}$	-50	—	Vdc
Emitter-Base Breakdown Voltage ( $I_E = -10 \mu\text{Adc}, I_C = 0$ )	$V_{(BR)EBO}$	-5.0	—	Vdc
Collector Cutoff Current	$I_{CEO}$	—	-100	nAdc
( $V_{CE} = -20 \text{ Vdc}, I_E = 0$ )		—	-10	$\mu\text{Adc}$
( $V_{CE} = -20 \text{ Vdc}, I_E = 0, T_A = 100^\circ\text{C}$ )		—	-10	$\mu\text{Adc}$

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

# DEVICE CHARACTERISTICS

## BCW70

### ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>ON CHARACTERISTICS</b>				
DC Current Gain ( $I_C = -2.0\text{ mAdc}$ , $V_{CE} = -5.0\text{ Vdc}$ )	$h_{FE}$			—
BCW69		120	260	
BCW70		215	500	
Collector–Emitter Saturation Voltage ( $I_C = -10\text{ mAdc}$ , $I_B = -0.5\text{ mAdc}$ )	$V_{CE(sat)}$	—	-0.3	Vdc
Base–Emitter On Voltage ( $I_C = -2.0\text{ mAdc}$ , $V_{CE} = -5.0\text{ Vdc}$ )	$V_{BE(on)}$	-0.6	-0.75	Vdc

### SMALL–SIGNAL CHARACTERISTICS

Output Capacitance ( $I_E = 0\text{ V}$ , $V_{CB} = -10\text{ Vdc}$ , $f = 1.0\text{ MHz}$ )	$C_{obo}$	—	7.0	pF
Noise Figure ( $V_{CE} = -5.0\text{ Vdc}$ , $I_C = -0.2\text{ mAdc}$ , $R_S = 2.0\text{ k}\Omega$ , $f = 1.0\text{ kHz}$ , $BW = 200\text{ Hz}$ )	$N_F$	—	10	dB

### Ordering Information

Device	Marking	Shipping
BCW69	H1	3000/Tape&Reel
BCW70	H2	3000/Tape&Reel

# DEVICE CHARACTERISTICS

## BCW70

### TYPICAL NOISE CHARACTERISTICS

( $V_{CE} = -5.0$  Vdc,  $T_A = 25^\circ\text{C}$ )

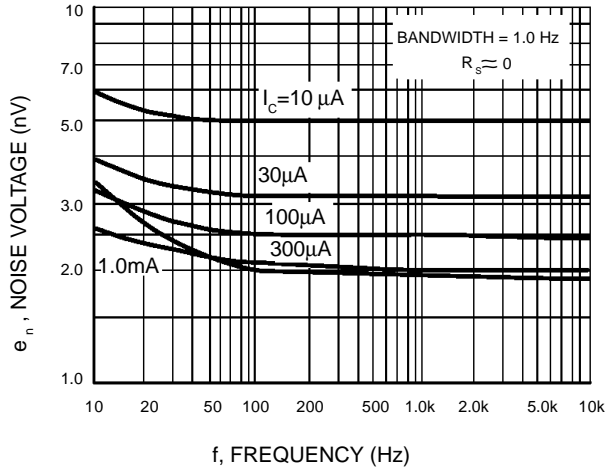


Figure 1. Noise Voltage

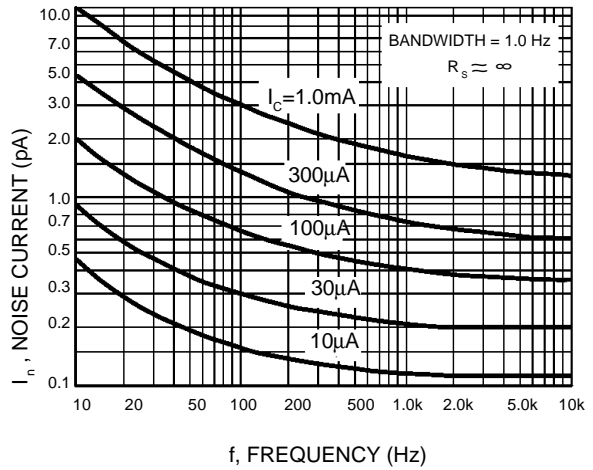


Figure 2. Noise Current

### NOISE FIGURE CONTOURS

( $V_{CE} = -5.0$  Vdc,  $T_A = 25^\circ\text{C}$ )

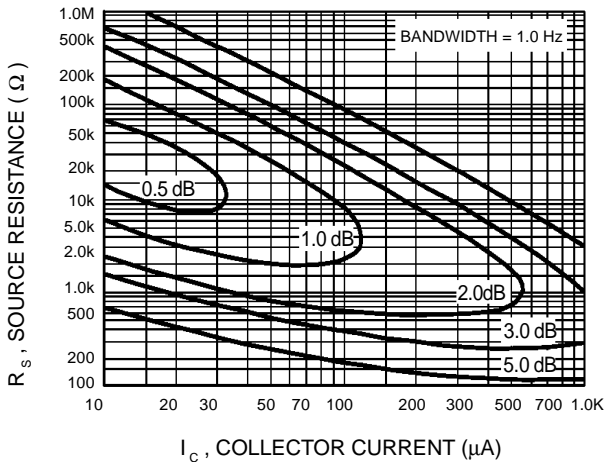


Figure 3. Narrow Band, 100 Hz

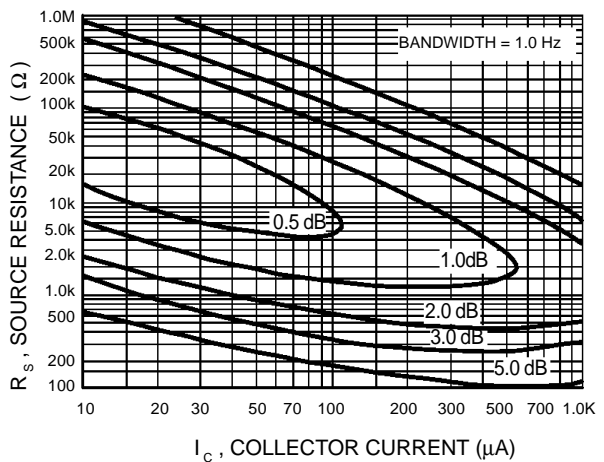


Figure 4. Narrow Band, 1.0 kHz

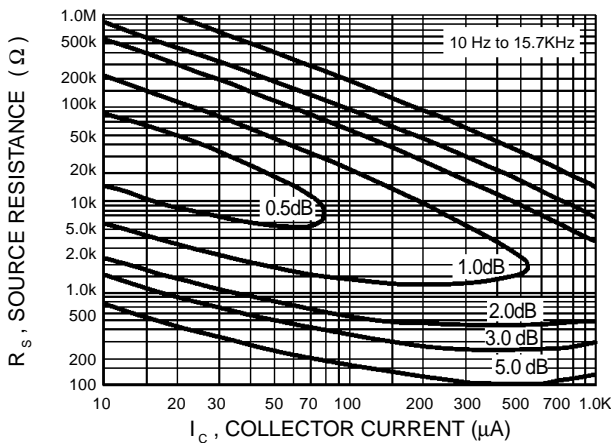


Figure 5. Wideband

Noise Figure is Defined as:

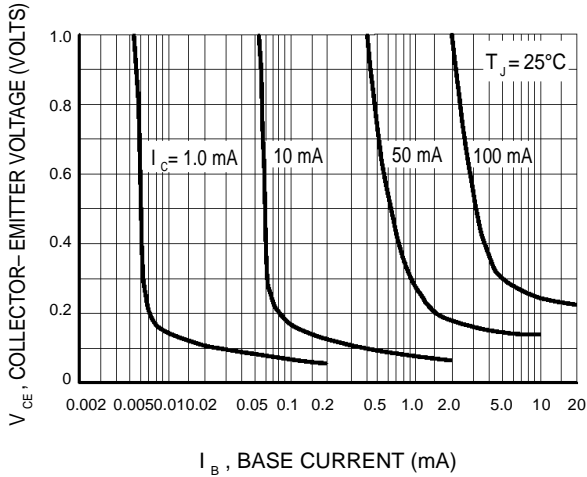
$$NF = 20 \log_{10} \left( \frac{e_n^2 + 4KTR_s + I_n^2 R_s^2}{4KTR_s} \right)^{1/2}$$

- $e_n$  = Noise Voltage of the Transistor referred to the input. (Figure 3)
- $I_n$  = Noise Current of the Transistor referred to the input. (Figure 4)
- $K$  = Boltzman's Constant ( $1.38 \times 10^{-23}$  j/°K)
- $T$  = Temperature of the Source Resistance (°K)
- $R_s$  = Source Resistance ( $\Omega$ )

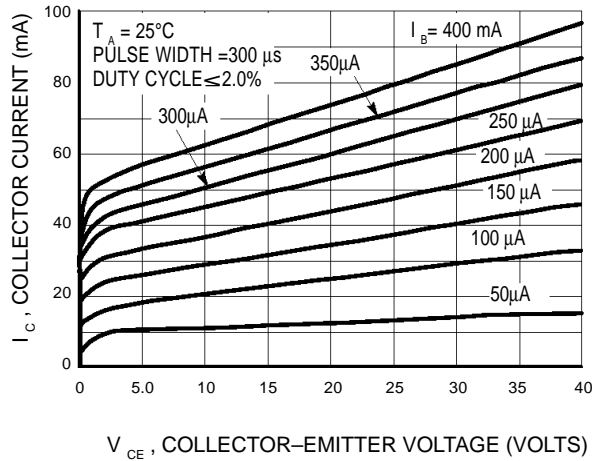
# DEVICE CHARACTERISTICS

## BCW70

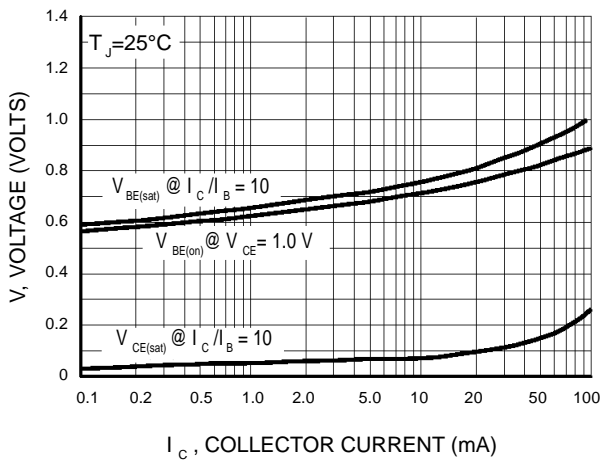
### TYPICAL STATIC CHARACTERISTICS



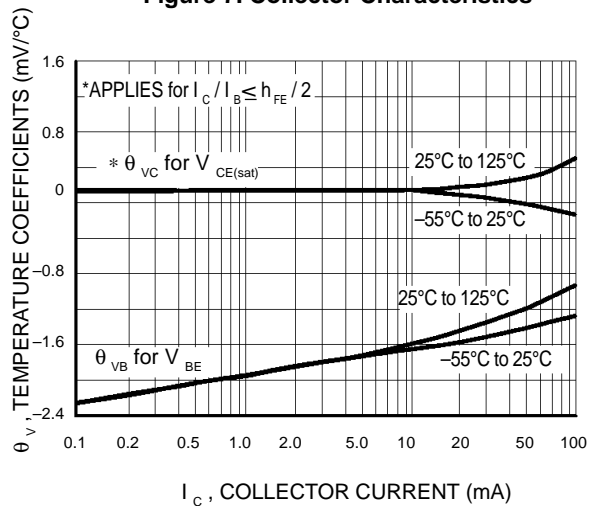
**Figure 6. Collector Saturation Region**



**Figure 7. Collector Characteristics**



**Figure 10. "On" Voltages**

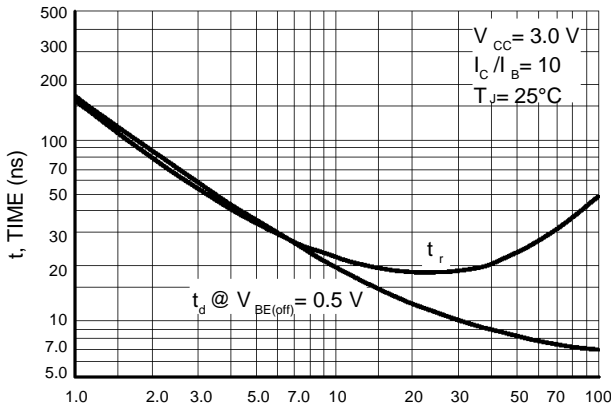


**Figure 11. Temperature Coefficients**

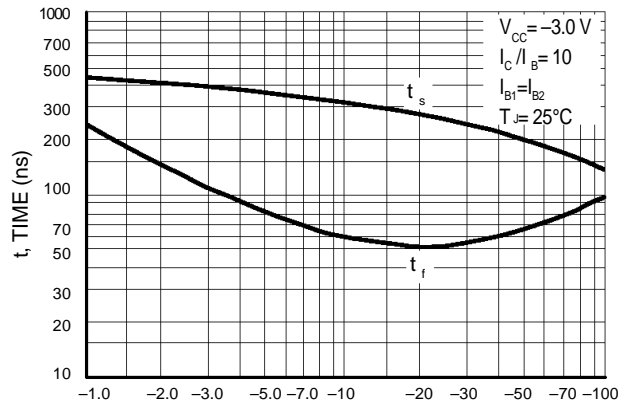
# DEVICE CHARACTERISTICS

## BCW70

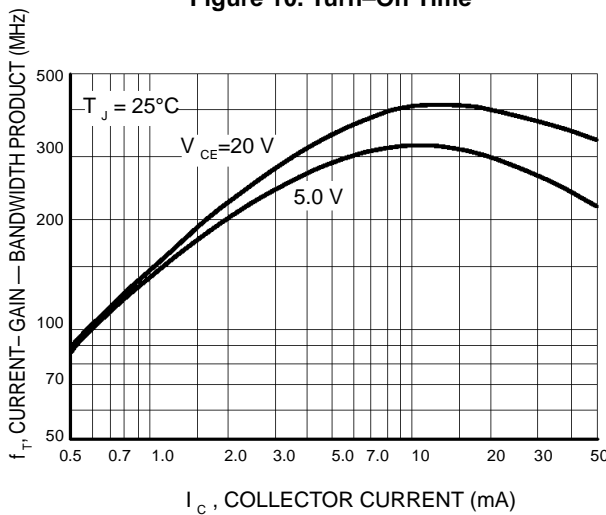
### TYPICAL DYNAMIC CHARACTERISTICS



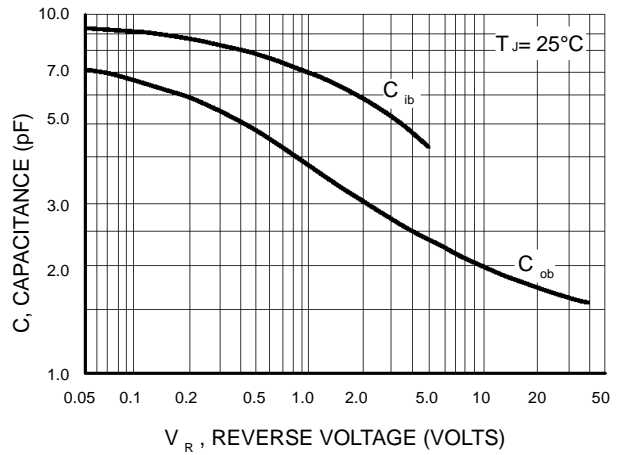
$I_C$ , COLLECTOR CURRENT (mA)  
Figure 10. Turn-On Time



$I_C$ , COLLECTOR CURRENT (mA)  
Figure 11. Turn-Off Time



$I_C$ , COLLECTOR CURRENT (mA)  
Figure 12. Current-Gain — Bandwidth Product



$V_R$ , REVERSE VOLTAGE (VOLTS)  
Figure 13. Capacitance

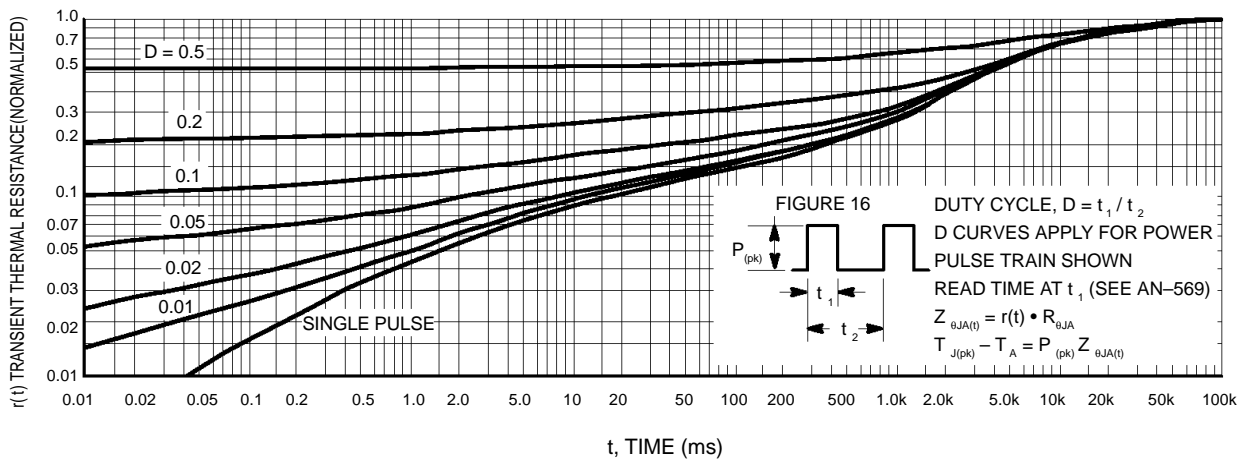


Figure 14. Thermal Response

# DEVICE CHARACTERISTICS

## BCW70

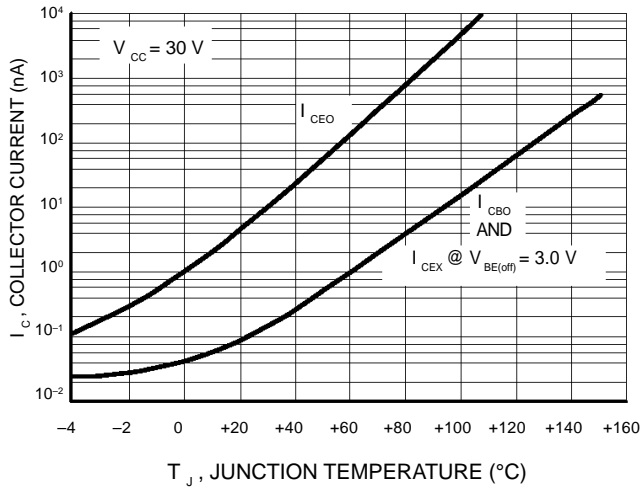


Figure 15. Typical Collector Leakage Current

### DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 16. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 14 was calculated for various duty cycles.

To find  $Z_{\theta JA(t)}$ , multiply the value obtained from Figure 14 by the steady state value  $R_{\theta JA}$ .

Example:

Dissipating 2.0 watts peak under the following conditions:

$t_1 = 1.0 \text{ ms}$ ,  $t_2 = 5.0 \text{ ms}$ . ( $D = 0.2$ )

Using Figure 14 at a pulse width of 1.0 ms and  $D = 0.2$ , the reading of  $r(t)$  is 0.22.

The peak rise in junction temperature is therefore

$$\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^{\circ}\text{C}.$$

For more information, see AN-569.

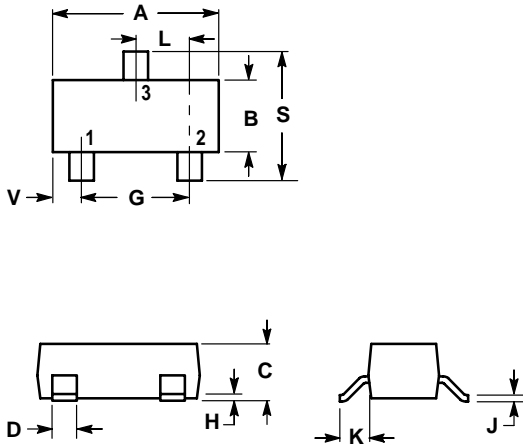
# PACKAGE OUTLINE & DIMENSIONS

## BCW70

### SOT-23

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

